

2SD1609, 2SD1610

Silicon NPN Epitaxial

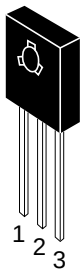
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Application

Low frequency high voltage amplifier complementary pair with 2SB1109 and 2SB1110

Outline

TO-126 MOD



- 1. Emitter
- 2. Collector
- 3. Base

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings		Unit
		2SD1609	2SD1610	
Collector to base voltage	V_{CBO}	160	200	V
Collector to emitter voltage	V_{CEO}	160	200	V
Emitter to base voltage	V_{EBO}	5	5	V
Collector current	I_C	100	100	mA
Collector power dissipation	P_C	1.25	1.25	W
Junction temperature	T_j	150	150	°C
Storage temperature	T_{stg}	-45 to +150	-45 to +150	°C

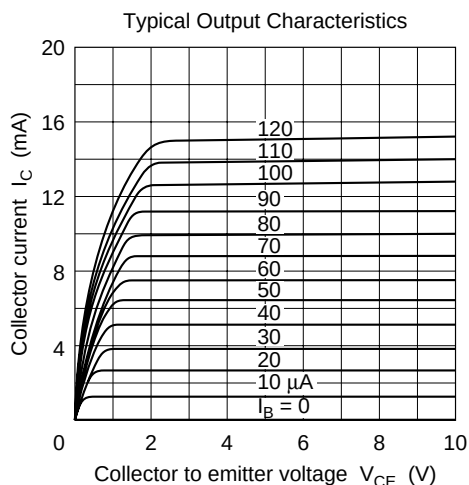
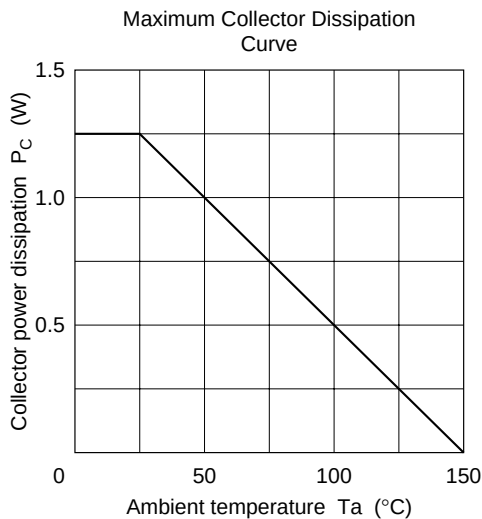
2SD1609, 2SD1610

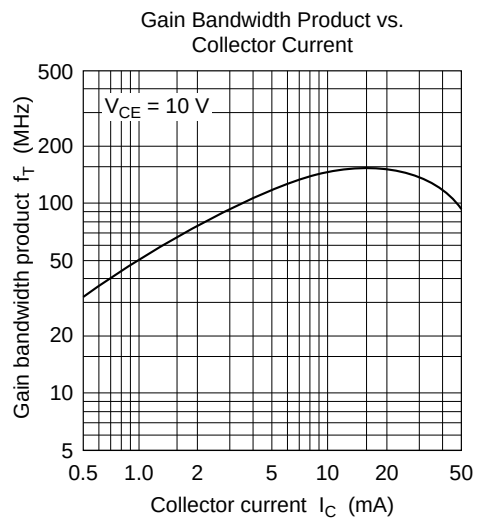
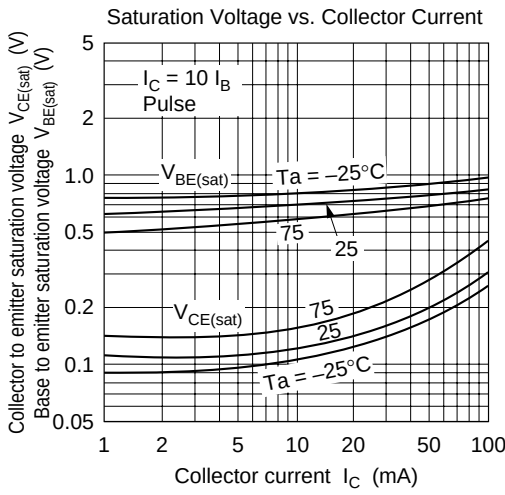
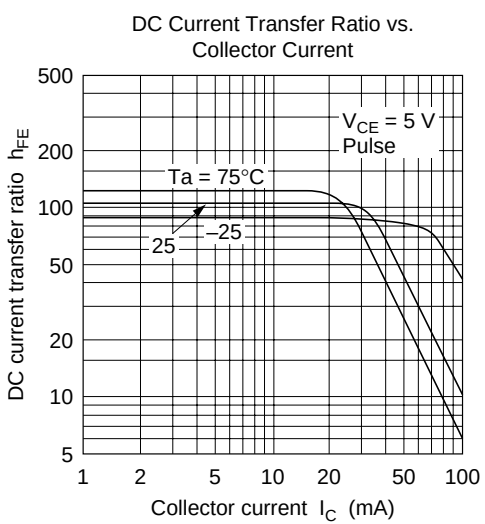
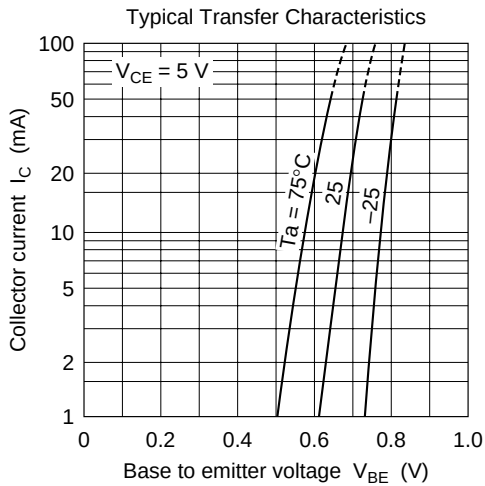
Electrical Characteristics (Ta = 25°C)

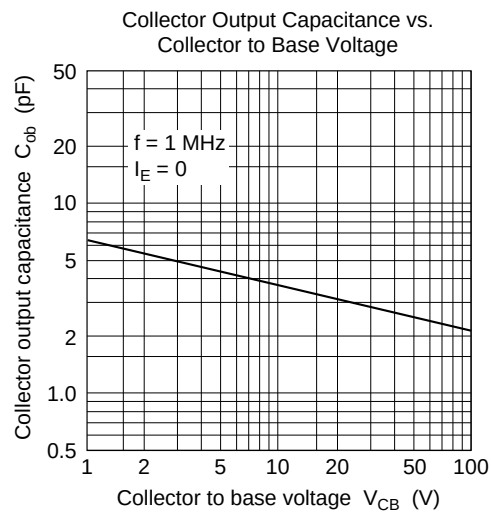
Item	Symbol	2SD1609			2SD1610			Unit	Test conditions
		Min	Typ	Max	Min	Typ	Max		
Collector to base breakdown voltage	$V_{(BR)CBO}$	160	—	—	200	—	—	V	$I_C = 10\text{ }\mu\text{A}, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	160	—	—	200	—	—	V	$I_C = 1\text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	—	—	5	—	—	V	$I_E = 10\text{ }\mu\text{A}, I_C = 0$
Collector cutoff current	I_{CBO}	—	—	10	—	—	—	μA	$V_{CB} = 140\text{ V}, I_E = 0$
		—	—	—	—	—	10		$V_{CB} = 160\text{ V}, I_E = 0$
DC current tarnsfer ratio	h_{FE1}^{*1}	60	—	320	60	—	320		$V_{CE} = 5\text{ V}, I_C = 10\text{ mA}$
	h_{FE2}	30	—	—	30	—	—		$V_{CE} = 5\text{ V}, I_C = 1\text{ mA}$
Base to emitter voltage	V_{BE}	—	—	1.5	—	—	1.5	V	$V_{CE} = 5\text{ V}, I_C = 10\text{ mA}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	2	—	—	2	V	$I_C = 30\text{ mA}, I_B = 3\text{ mA}$
Gain bandwidth product	f_T	—	140	—	—	140	—	MHz	$V_{CE} = 5\text{ V}, I_C = 10\text{ mA}$
Collector output capacitance	C_{ob}	—	3.8	—	—	3.8	—	pF	$V_{CB} = 10\text{ V}, I_E = 0, f = 1\text{ MHz}$

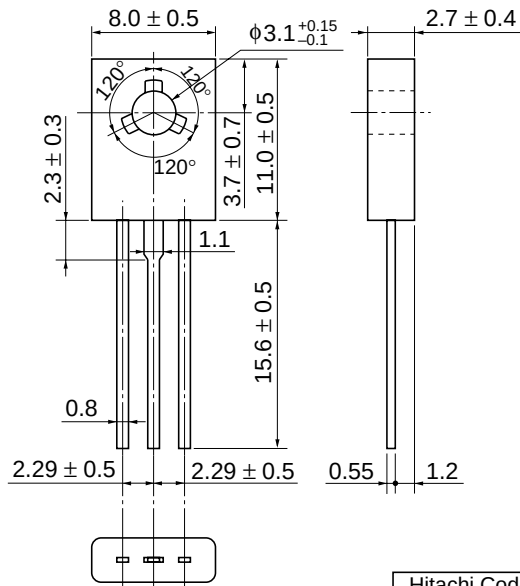
Note: 1. The 2SD1609 and 2SD1610 are grouped by h_{FE1} as follows.

B	C	D
60 to 120	100 to 200	160 to 320









Hitachi Code	TO-126 Mod
JEDEC	—
EIAJ	—
Weight (reference value)	0.67 g

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Hitachi, Ltd.

Semiconductor & Integrated Circuits.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

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For further information write to:

Hitachi Semiconductor (America) Inc. 179 East Tasman Drive, San Jose, CA 95134 Tel: <1> (408) 433-1990 Fax: <1> (408) 433-0223	Hitachi Europe GmbH Electronic components Group Dornacher Straße 3 D-85622 Feldkirchen, Munich Germany Tel: <49> (89) 9 9180-0 Fax: <49> (89) 9 29 30 00 Hitachi Europe Ltd. Electronic Components Group. Whitebrook Park Lower Cookham Road Maidenhead Berkshire SL6 8YA, United Kingdom Tel: <44> (1628) 585000 Fax: <44> (1628) 778322
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Hitachi Asia Pte. Ltd. 16 Collyer Quay #20-00 Hitachi Tower Singapore 049318 Tel: 535-2100 Fax: 535-1533 Hitachi Asia Ltd. Taipei Branch Office 3F, Hung Kuo Building. No.167, Tun-Hwa North Road, Taipei (105) Tel: <886> (2) 2718-3666 Fax: <886> (2) 2718-8180
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Hitachi Asia (Hong Kong) Ltd. Group III (Electronic Components) 7/F., North Tower, World Finance Centre, Harbour City, Canton Road, Tsim Sha Tsui, Kowloon, Hong Kong Tel: <852> (2) 735 9218 Fax: <852> (2) 730 0281 Telex: 40815 HITEC HX
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